

## Silicon NPN Power Transistors

2SC2027

**DESCRIPTION**

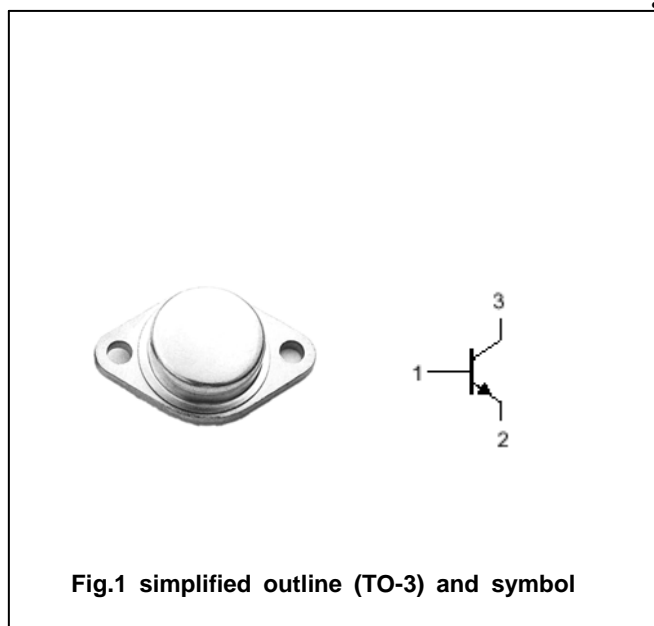
- With TO-3 package
- High voltage ,high speed

**APPLICATIONS**

- For high voltage ,power switching and TV horizontal output applications

**PINNING(see fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	800	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		5	A
I <sub>CM</sub>	Collector current-peak		7.5	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25°C	50	W
T <sub>j</sub>	Junction temperature		175	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A; I <sub>B</sub> =0	800			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.0 A; I <sub>B</sub> =1.3 A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.0 A; I <sub>B</sub> =1.3 A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =600V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8		36	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4.5A ; V <sub>CE</sub> =5V	2.25			

PACKAGE OUTLINE

